

DIODE

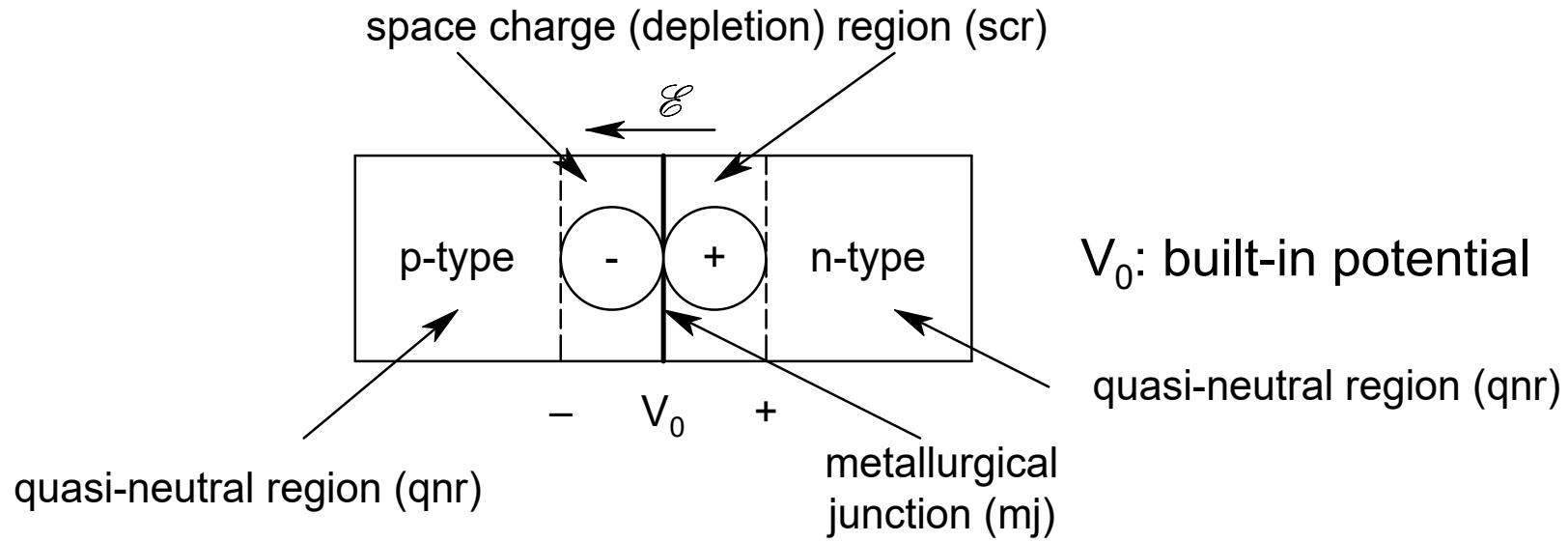
p-type
(N_A)

n-type
(N_D)

N_A : Acceptor Doping
 N_D : Donor Doping

Before Joining

- ***p-side:***
 - *Holes majority carriers*
 - *Electrons minority carriers*
- ***n-side:***
 - *Electrons majority carriers*
 - *Holes minority carriers*
- ***Holes: Anti-particles of electrons***



After Joining (In Equilibrium)

- ***Dissociation Relations:***

$$N_A \leftrightarrow N_A^- + \text{hole}$$

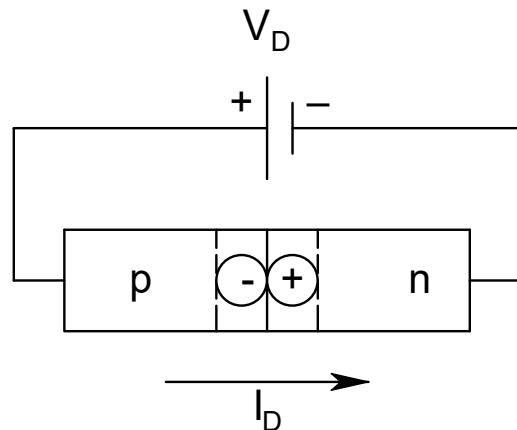
$$N_D \leftrightarrow N_D^+ + \text{electron}$$

Establishment of Equilibrium

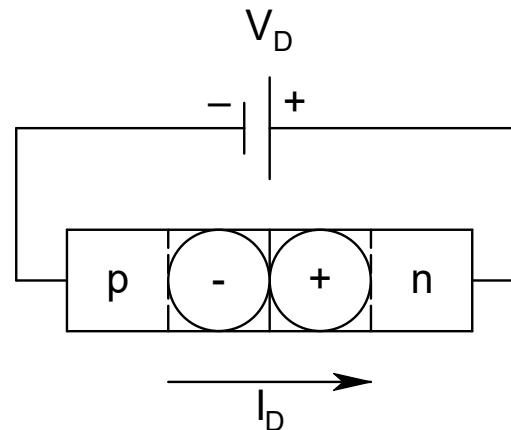
- *Holes diffuse from p to n*
 - *Negatively charged acceptor ions uncovered near MJ*
- *Electrons diffuse from n to p*
 - *Positively charged donor ions uncovered near MJ*
- *Establishment of a charge dipole around MJ*
 - *Generation of an electric field \mathcal{E} around MJ*
 - *Creation of built-in potential V_0*

- *E creates drift components of carriers*
 - *Holes pushed back to p*
 - *Electrons pushed back to n*
- When these two motions (*drift and diffusion*) completely *balance out*
 - *Equilibrium* is reached
- Under this condition, the *net fluxes* of *both electrons and holes* across MJ are *zero*
 - *No net current flows through the device*

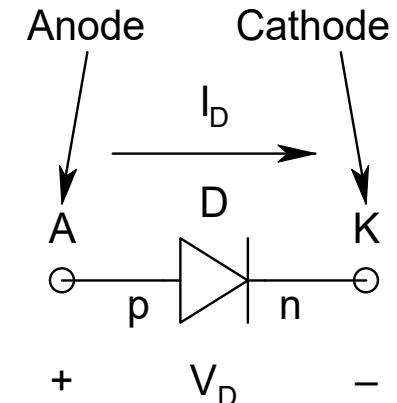
Diode Under Bias



Forward Bias:
p-side positive
w.r.t. n-side



Reverse Bias:
n-side positive
w.r.t. p-side



**Symbol and
current-voltage
convention**

Voltage and Current Conventions :

V_D : 0 (Equilibrium), Positive (Forward Bias), Negative (Reverse Bias)

I_D : p to n (Positive), n to p (Negative)